RT1P44QX SERIES

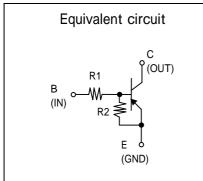
Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

DESCRIPTION OUTLINE DRAWING UNIT: mm RT1P44QX is a one chip transistor RT1P44QC RT1P44QU with built-in bias resistor,NPN type is RT1N44QX. 1.6 2.5 0.8 1.5 0.4 0.4 0.5 0.5 **FEATURE** •Built-in bias resistor (R1=47k ,R2=10k). 2 90 9. 0 2.9 **APPLICATION** 0.55 8.0 Equivalent circuit 0.7 <u>.</u> ~ ∼ 0 С JEITA: -JEITA: SC-59 (OUT) R1 JEDEC: -JEDEC: Similar to TO-236 В **Terminal Connector Terminal Connector** (IN) : Base : Base R2 : Emitter : Emitter : Collector : Collector Е (GND) RT1P44QM RT1P44QS 4.0 2.1 1.25 0.425 0.425 3.0 3 0.1 2.0 14.0 <u>~</u> 0.45 1.27 1.27 2.5 51 ~0 JEITA: SC-70 JEITA: -JEDEC: -JEDEC: -**Terminal Connector Terminal Connector** : Emitter : Base : Emitter : Collector : Collector : Base

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Inverted circuit, switching circuit, interface circuit, driver circuit.





RT1P44QX SERIES

Transistor Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

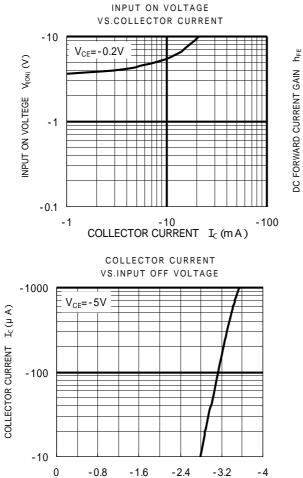
MAXIMUM RATING (Ta=25)

SYMBOL	PARAMETER	RATING				UNIT
		RT1P44QU	RT1P44QM	RT1P44QC	RT1P44QS	UNIT
V _{CBO}	Collector to Base voltage	-50				
V _{EBO}	Emitter to Base voltage	-15				
V _{CEO}	Collector to Emitter voltage	-50				V
I _c	Collector current	-100				
I _{CM}	Peak Collector current	-200				mA
P _c	Collector dissipation(Ta=25)	150	2	00	450	mW
Tj	Junction temperature	+150	150 +150			
Tstg	Storage temperature	-55 ~ +150	-55 ~ +150			

ELECTRICAL CHARACTERISTICS (Ta=25)

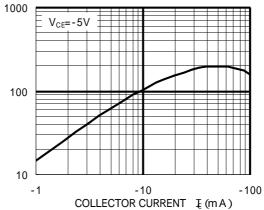
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
V _{(BR)CEO}	C to E break down voltage	Ι _c =-100 μ A , R _{BE} =	-50			V
I _{CBO}	Collector cut off current	V _{CB} =-50V , I _E =0			-0.1	μA
h _{FE}	DC forward current gain	V _{CE} =-5V , I _C =-5mA	33			-
$V_{CE(sat)}$	C to E saturation voltage	I _c =-10mA , I _B =-0.5mA			-0.3	V
V _{I(ON)}	Input on voltage	V _{CE} =-0.2V , I _C =-5mA		-4.2	-8.9	V
V _{I(OFF)}	Input off voltage	V _{CE} =-5V , I _C =-100 μ A	-2.3	-3.1		V
R ₁	Input resistance		33	47	61	k
R_2 / R_1	Resistance ratio		0.17	0.21	0.26	
f _T	Gain band width product	V _{CE} =-6V , I _E =10mA		150		MHz

TYPICAL CHARACTERISTICS



INPUT OFF VOLTAGE $V_{I(OFF)}(V)$

DC FORWARD CURRENT GAIN VS.COLLECTOR CURRENT





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